# 300 mA CMOS LDO with Shutdown and V<sub>REF</sub> Bypass

The NCP4569 is a fixed output, high accuracy (typically  $\pm 0.5\%$ ) CMOS upgrade for older (bipolar) low dropout regulators. Total supply current is typically 50  $\mu A$  at full load (20 to 60 times lower than in bipolar regulators).

NCP4569 key features include ultra low noise operation (plus optional Bypass input); very low dropout voltage (typically 240 mV at full load), and fast response to step changes in load. Supply current is reduced to 0.05  $\mu$ A (typical) and  $V_{OUT}$  falls to zero when the shutdown input is low.

The NCP4569 incorporates both over–temperature and over–current protection. The NCP4569 is stable with an output capacitor of only  $1.0 \,\mu\text{F}$  and has a maximum output current of  $300 \,\text{mA}$ .

## **Features**

- Zero Ground Current for Longer Battery Life
- Very Low Dropout Voltage
- Guaranteed 300 mA Output
- High Output Voltage Accuracy
- Standard or Custom Output Voltages
- Power-Saving Shutdown Mode
- Bypass Input for Ultra-Quiet Operation
- Over-Current and Over-Temperature Protection
- Space–Saving Micro–8 Package

## **Applications**

- Battery-Operated Systems
- Portable Computers
- Medical Instruments
- Instrumentation
- Cellular/GSM/PHS Phones
- Linear Post–Regulator for SMPS
- Pagers
- Digital Cameras

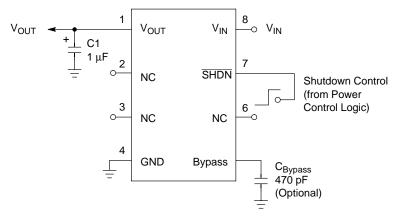
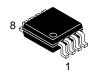


Figure 1. Typical Application



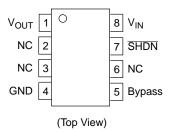
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MICRO-8 DM SUFFIX CASE 846A

#### PIN CONFIGURATION



## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

#### **ABSOLUTE MAXIMUM RATINGS\***

	Symbol	Value	Unit	
Input Voltage			6.5	V
Output Voltage			$V_{SS} - 0.3$ to $V_{IN} + 0.3$	_
Power Dissipation		-	Internally Limited (Note 8.)	-
Operating Temperature		T <sub>A</sub>	$-40 < T_{J} < 125$	°C
Storage Temperature		T <sub>stg</sub>	-65 to +150	°C
Maximum Voltage on any Pin		-	V <sub>IN</sub> + 0.3 to - 0.3	V
Lead Temperature (Soldering, 1	0 Sec.)	-	+300	°C
ESD Withstand Voltage Human Body Model (Note 1.)		V <sub>ESD</sub>	>2000	V
Latch–Up Performance (Note 2.	) Positive Negative	I <sub>LATCH</sub> -UP	> 500 > 500	mA

<sup>\*</sup>Absolute Maximum Ratings indicate device operation limits beyond damage may occur. Device operation beyond the limits listed in Electrical Characteristics is not recommended.

- 1. Tested to EIA/JESD22-A114-A
- 2. Tested to EIA/JESD78

**ELECTRICAL CHARACTERISTICS** ( $V_{IN} = V_{OUT} + 1.0 \text{ V}$ ,  $I_L = 0.1 \mu\text{A}$ ,  $C_L = 3.3 \mu\text{F}$ ,  $\overline{\text{SHDN}} > V_{IH}$ ,  $T_A = 25^{\circ}\text{C}$ , unless otherwise noted. **Boldface** type specifications apply for junction temperatures of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ .)

Characteristics	Test Conditions	Symbol	Min	Тур	Max	Unit
Input Operating Voltage	ut Operating Voltage -		-	-	6.0	V
Maximum Output Current	-	I <sub>OUTMAX</sub>	300	-	-	mA
Output Voltage	Note 3.	V <sub>OUT</sub>	- V <sub>R</sub> - 2.5%	V <sub>R</sub> ± 0.5%	- V <sub>R</sub> + 2.5%	V
V <sub>OUT</sub> Temperature Coefficient	Note 4.	$\Delta V_{OUT}/\Delta T$	-	40	_	ppm/°C
Line Regulation	$(V_R + 1.0 \text{ V}) \le V_{IN} \le 6.0 \text{ V}$	$\Delta V_{OUT}/\Delta V_{IN}$	-	0.05	0.35	%
Load Regulation	$I_L = 0.1 \text{ mA to } I_{OUTMAX}$	$\Delta V_{OUT}/V_{OUT}$	-	0.5	2.0	%
Dropout Voltage	$I_L = 0.1 \text{ mA}$ $I_L = 100 \text{ mA}$ $I_L = 300 \text{ mA}$ Note 6.	V <sub>IN</sub> – V <sub>OUT</sub>	- - -	20 80 240	30 160 480	mV
Supply Current SHDN = V <sub>IH</sub>		I <sub>SS1</sub>	-	50	90	μΑ
Shutdown Supply Current	SHDN = 0 V	I <sub>SS2</sub>	-	0.05	0.5	μΑ
Power Supply Rejection Ratio $F_{RE} \le 1.0 \text{ kHz}$		PSRR	-	60	_	dB
Output Short Circuit Current V <sub>OUT</sub> = 0 V		l <sub>outsc</sub>	-	550	650	mA
Thermal Regulation Note 7.		$\Delta V_{OUT}/\Delta P_{D}$	_	0.04	-	V/W
Output Noise	$F = 1.0 \text{ kHz}, C_{OUT} = 1.0 \mu\text{F},$ $R_{LOAD} = 50 \Omega$	eN	-	260	_	nV/√Hz

## **SHDN** Input

SHDN Input High Threshold	-	V <sub>IH</sub>	45	_	_	%V <sub>IN</sub>
SHDN Input Low Threshold	_	$V_{IL}$	_	-	15	%V <sub>IN</sub>

- 3.  $V_R$  is the regulator output voltage setting.
- 4.  $T_C V_{OUT} = \frac{(V_{OUTMAX} V_{OUTMIN}) \times 10^6}{V_{OUT} \times \Delta T}$
- 5. Regulation is measured at a constant junction temperature using low duty cycle pulse testing. Load regulation is tested over a load range from 0.1 mA to the maximum specified output current. Changes in output voltage due to heating effects are covered by the thermal regulation specification.
- 6. Dropout voltage is defined as the input to output differential at which the output voltage drops 2% below its nominal value measured at a 1.0 V differential.
- 7. Thermal Regulation is defined as the change in output voltage at a time T after a change in power dissipation is applied, excluding load or line regulation effects. Specifications are for a current pulse equal to I<sub>LMAX</sub> at V<sub>IN</sub> = 6.0 V for T = 10 msec.
- 8. The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature, and the thermal resistance from junction–to–air (i.e. T<sub>A</sub>, T<sub>J</sub>, θ<sub>JA</sub>). Exceeding the maximum allowable power dissipation causes the device to initiate thermal shutdown. Please see *Thermal Considerations* section of this data sheet for more details.

### **DETAILED DESCRIPTION**

The NCP4569 is a precision regulator available in fixed voltages. Unlike the bipolar regulators, the NCP4569 supply current does not increase with load current. In addition, V<sub>OUT</sub> remains stable and within regulation at very low load

currents (an important consideration in RTC and CMOS RAM battery backup applications). NCP4569 pin functions are detailed below.

### **PIN DESCRIPTION**

Pin Number	Symbol	Description
1	V <sub>OUT</sub>	Regulated voltage output.
2	NC	No connect.
3	NC	No connect.
4	GND	Ground terminal.
5	Bypass	Reference bypass input. Connecting a 470 pF to this input further reduces output noise.
6	NC	No connect.
7	SHDN	Shutdown control input. The regulator is fully enabled when a logic high is applied to this input. The regulator enters shutdown when a logic low is applied to this input. During shutdown, output voltage falls to zero and supply current is reduced to 0.05 µA (typical).
8	V <sub>IN</sub>	Unregulated supply input.

Figure 2 shows a typical application circuit. The regulator is enabled any time the shutdown input ( $\overline{SHDN}$ ) is at or above  $V_{IH}$ , and shutdown (disabled) when  $\overline{SHDN}$  is at or below  $V_{IL}$ .  $\overline{SHDN}$  may be controlled by a CMOS logic gate,

or I/O port of a microcontroller. If the  $\overline{SHDN}$  input is not required, it should be connected directly to the input supply. While in shutdown, supply current decreases to 0.05  $\mu A$  (typical),  $V_{OUT}$  falls to zero.

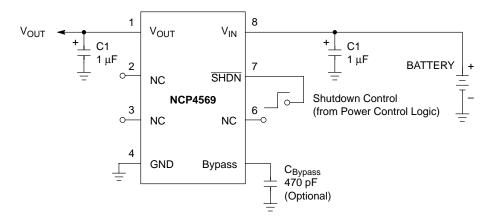


Figure 2. Typical Application Circuit

## **Bypass Input**

A 470 pF capacitor connected from the Bypass input to ground reduces noise present on the internal reference, which in turn significantly reduces output noise. If output noise is not a concern, this input may be left unconnected. Larger capacitor values may be used, but results in a longer time period to rated output voltage when power is initially applied.

## **Output Capacitor**

A 1.0  $\mu F$  (min) capacitor from  $V_{OUT}$  to ground is recommended. The output capacitor should have an effective series resistance of 5.0  $\Omega$  or less, and a resonant

frequency above 1.0 MHz. A 1.0  $\mu F$  capacitor should be connected from  $V_{IN}$  to GND if there is more than 10 inches of wire between the regulator and the AC filter capacitor, or if a battery is used as the power source. Aluminum electrolytic or tantalum capacitor types can be used. (Since many aluminum electrolytic capacitors freeze at approximately  $-30^{\circ}C$ , solid tantalums are recommended for applications operating below  $-25^{\circ}C$ .) When operating from sources other than batteries, supply–noise rejection and transient response can be improved by increasing the value of the input and output capacitors and employing passive filtering techniques.

### **Thermal Considerations**

#### Thermal Shutdown

Integrated thermal protection circuitry shuts the regulator off when die temperature exceeds 150°C. The regulator remains off until the die temperature drops to approximately 140°C.

## **Power Dissipation**

The amount of power the regulator dissipates is primarily a function of input and output voltage, and output current. The following equation is used to calculate worst case *actual* power dissipation:

Where :  $P_D$  = worst case actual power dissipation  $V_{INMAX}$  = maximum voltage on  $V_{IN}$ 

VOUTMIN = minimum regulator output voltage ILOADMAX = maximum output (load) current

(eq. 1)

The maximum *allowable* power dissipation (Equation 2) is a function of the maximum ambient temperature ( $T_{AMAX}$ ), the maximum allowable die temperature ( $125^{\circ}C$ ), and the thermal resistance from junction—to—air ( $\theta_{JA}$ ). The Micro—8 package has a  $\theta_{JA}$  of approximately **200°C/Watt**; both when mounted on a single layer FR4 dielectric copper clad PC board.

$$P_{DMAX} = \frac{(T_{JMAX} - T_{AMAX})}{\theta_{JA}}$$

Where all terms are previously defined. (eq. 2)

Equation 1 can be used in conjunction with Equation 2 to ensure regulator thermal operation is within limits. For example:

GIVEN: 
$$\begin{aligned} \text{VINMAX} &= 3.0 \text{ V} \pm 10\% \\ \text{VOUTMIN} &= 2.7 \text{ V} - 2.5\% \\ \text{ILOAD} &= 250 \text{ mA} \\ \text{TAMAX} &= 55^{\circ}\text{C} \end{aligned}$$

Micro-8 Package

FIND: 1. Actual power dissipation.

2. Maximum allowable dissipation.

Actual power dissipation:

$$P_D \approx (V_{INMAX} - V_{OUTMIN})I_{LOADMAX}$$
  
=  $[(3.0 \times 1.1) - (2.7 \times .975)]250 \times 10^{-3}$   
= 167 mW

Maximum allowable power dissipation:

$$P_{DMAX} = \frac{(T_{JMAX} - T_{AMAX})}{\theta_{JA}}$$
$$= (\underline{125 - 55})$$
$$\underline{200}$$
$$= 350 \text{ mW}$$

In this example, the NCP4569 dissipates a maximum of only 167 mW; far below the allowable limit of 350 mW. In a similar manner, Equation 1 and Equation 2 can be used to calculate maximum current and/or input voltage limits.

## **Layout Considerations**

The primary path of heat conduction out of the package is via the package leads. Therefore, layouts having a ground plane, wide traces at the pads, and wide power supply bus lines combine to lower  $\theta_{JA}$  and, therefore, increase the maximum allowable power dissipation limit.

## **TYPICAL CHARACTERISTICS**

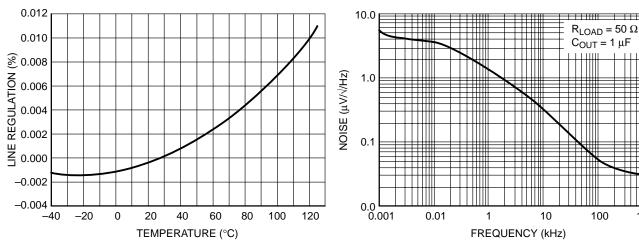


Figure 3. Line Regulation

Figure 4. Output Noise

1000

100

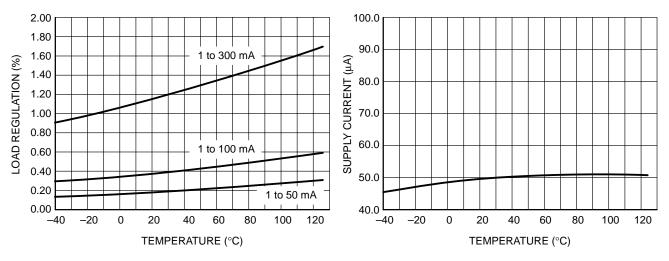


Figure 5. Load Regulation

Figure 6. Supply Current

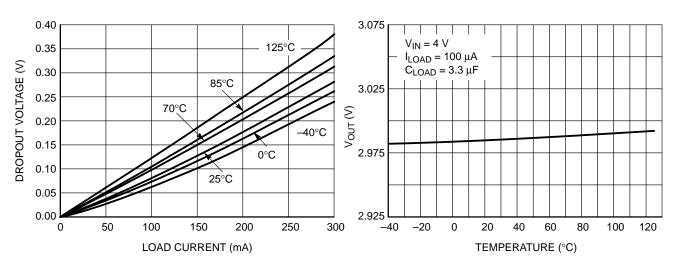


Figure 7. Dropout Voltage vs. Load Current

Figure 8. V<sub>OUT</sub> vs. Temperature

## **TYPICAL CHARACTERISTICS**

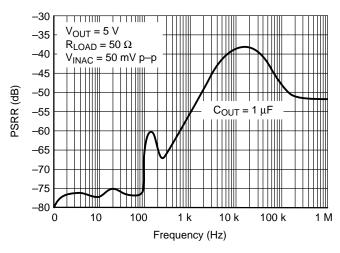
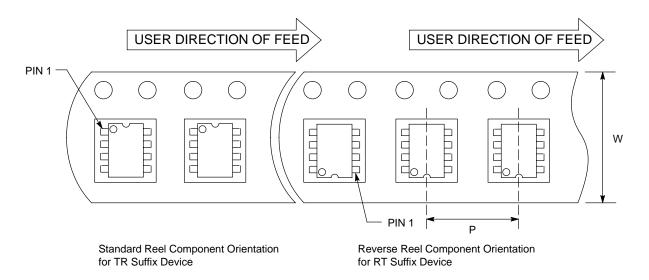


Figure 9. Power Supply Rejection Ratio

## **Component Taping Orientation for Micro-8 Devices**



## Carrier Tape, Number of Components Per Reel and Reel Size

Package	Carrier Width (W)	Pitch (P)	Part Per Full Reel	Reel Size
Micro-8	12 mm	8 mm	2500	13 inches

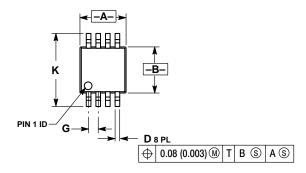
## ORDERING INFORMATION

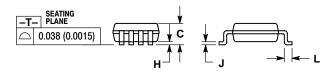
Device	Output Voltage (V)*	Package	Junction Temperature Range	Shipping
NCP4569DM25R2	2.5			
NCP4569DM28R2	2.8			
NCP4569DM30R2	3.0	Micro-8	–40°C to + 125°C	2500 Tape & Reel
NCP4569DM33R2	3.3			
NCP4569DM50R2	5.0			

<sup>\*</sup>Other output voltages available. Please contact ON Semiconductor for details.

## **PACKAGE DIMENSIONS**

## MICRO-8 DM SUFFIX CASE 846A-02 ISSUE E





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   V14 5M 1982
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	2.90	3.10	0.114	0.122	
В	2.90	3.10	0.114	0.122	
С		1.10		0.043	
D	0.25	0.40	0.010	0.016	
G	0.65	BSC	0.026	BSC	
Н	0.05	0.15	0.002	0.006	
J	0.13	0.23	0.005	0.009	
K	4.75	5.05	0.187	0.199	
L	0.40	0.70	0.016	0.028	

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